



(51) International Patent Classification:

G06F 1/32 (2006.01) H01L 27/105 (2006.01)
H01L 21/336 (2006.01) H01L 27/108 (2006.01)
H01L 21/822 (2006.01) H01L 27/115 (2006.01)
H01L 21/8242 (2006.01) H01L 29/786 (2006.01)
H01L 21/8247 (2006.01) H01L 29/788 (2006.01)
H01L 27/04 (2006.01) H01L 29/792 (2006.01)
H01L 27/10 (2006.01)

(21) International Application Number:

PCT/JP2013/051230

(22) International Filing Date:

16 January 2013 (16.01.2013)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

2012-011124	23 January 2012 (23.01.2012)	JP
2012-011120	23 January 2012 (23.01.2012)	JP
2012-105538	3 May 2012 (03.05.2012)	JP

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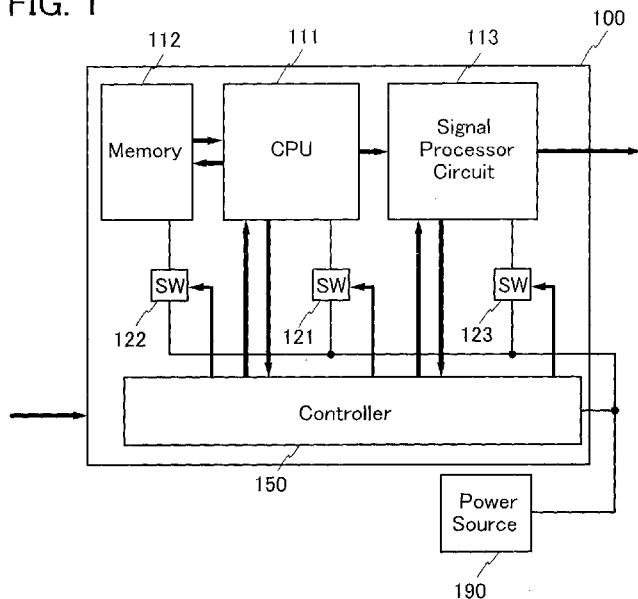
(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY,
BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM,
DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT,
HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR,
KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME,
MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ,
OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC,
SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ,
UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ,
TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,
EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV,
MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,
TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,
ML, MR, NE, SN, TD, TG).

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(54) Title: SEMICONDUCTOR DEVICE

FIG. 1



(57) Abstract: To individually control supply of the power supply voltage to circuits, a semiconductor device includes a CPU, a memory that reads and writes data used in arithmetic operation of the CPU, a signal processing circuit that generates an output signal by converting a data signal generated by the arithmetic operation of the CPU, a first power supply control switch that controls supply of the power supply voltage to the CPU, a second power supply control switch that controls supply of the power supply voltage to the memory, a third power supply control switch that controls supply of the power supply voltage to the signal processing circuit, and a controller that at least has a function of controlling the first to third power supply control switches individually in accordance with an input signal and instruction signals input from the CPU and the signal processing circuit.



Published:

— *with international search report (Art. 21(3))*